

## Product Summary

$BV_{DSS}$	$R_{DS(ON)}$ max	$I_D$ max $T_C = +25^\circ\text{C}$
100V	28m $\Omega$ @ $V_{GS} = 10\text{V}$	60A

## Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

## Applications

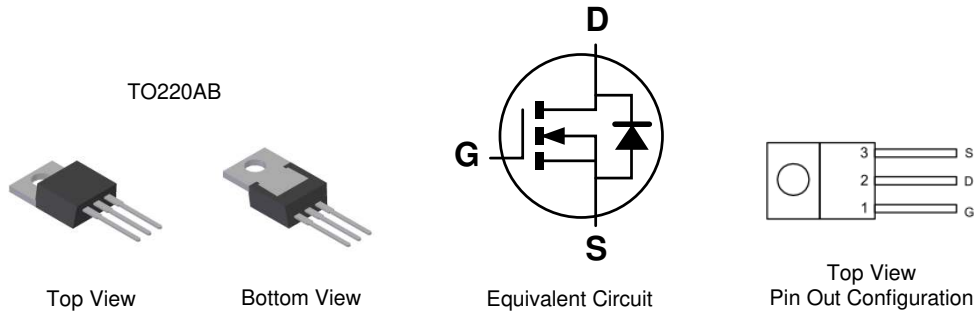
- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

## Features

- Rated to  $+175^\circ\text{C}$  – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – ensures more reliable and robust end application
- Low Input Capacitance
- Low Input/Output Leakage
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: TO220AB
- Case Material: Molded Plastic, “Green” Molding Compound, UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 <sup>(3)</sup>
- Terminal Connections: See Diagram Below
- Weight: TO220AB – 1.85 grams (Approximate)

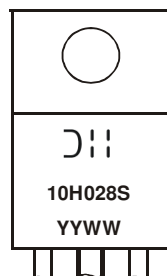


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH10H028SCT	TO220AB	50 pieces/tube

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated’s definitions of Halogen- and Antimony-free, “Green” and Lead-free.
  3. Halogen- and Antimony-free “Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



= Manufacturer's Marking  
 10H028S = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 16 = 2016)  
 WW = Week (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	100	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V	I <sub>D</sub>	T <sub>C</sub> = +25°C	60
		T <sub>C</sub> = +100°C	42
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	90	A
Maximum Continuous Body Diode Forward Current (Note 5)	I <sub>S</sub>	2.8	A
Avalanche Current, L = 0.1mH	I <sub>AS</sub>	27	A
Avalanche Energy, L = 0.1mH	E <sub>AS</sub>	37	mJ

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	2.8	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	54	°C/W
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	1	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current, T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2.0	2.8	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	19	28	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.0A
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	1942	—	pF	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	166	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	47	—	pF	
Gate Resistance	R <sub>g</sub>	—	1.8	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 8V)	Q <sub>g</sub>	—	25.4	—	nC	V <sub>DS</sub> = 50V, I <sub>D</sub> = 20A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	31.9	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	8.1	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	6.5	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	7.1	—	ns	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 50V, R <sub>G</sub> = 3Ω, I <sub>D</sub> = 20A
Turn-On Rise Time	t <sub>R</sub>	—	6.6	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	14.0	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	3.2	—	ns	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	35.3	—	ns	I <sub>F</sub> = 20A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	46.8	—	nC	I <sub>F</sub> = 20A, di/dt = 100A/µs

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.  
6. Short duration pulse test used to minimize self-heating effect.  
7. Guaranteed by design. Not subject to product testing.

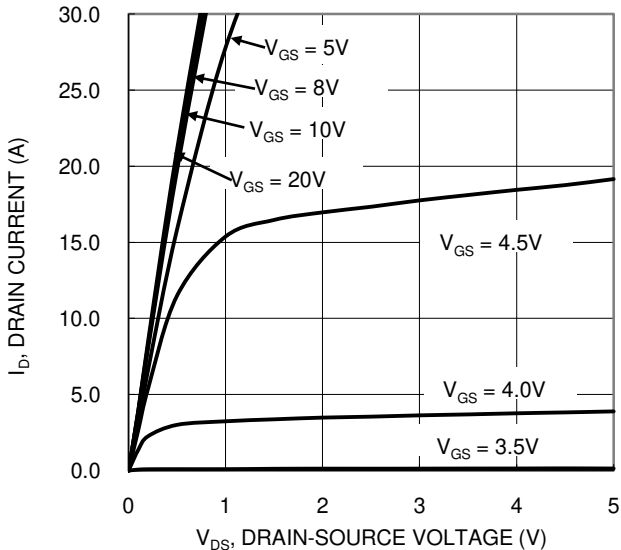


Figure 1. Typical Output Characteristic

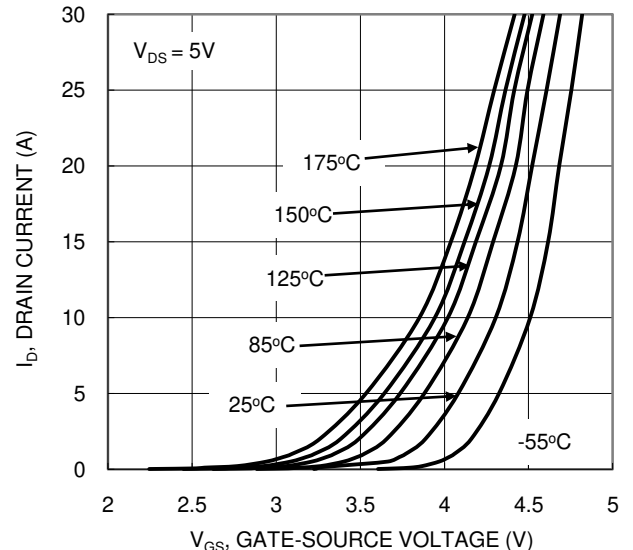


Figure 2. Typical Transfer Characteristic

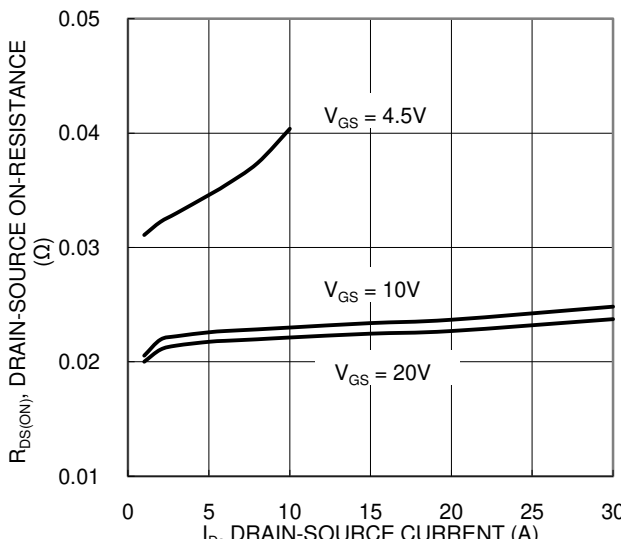


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

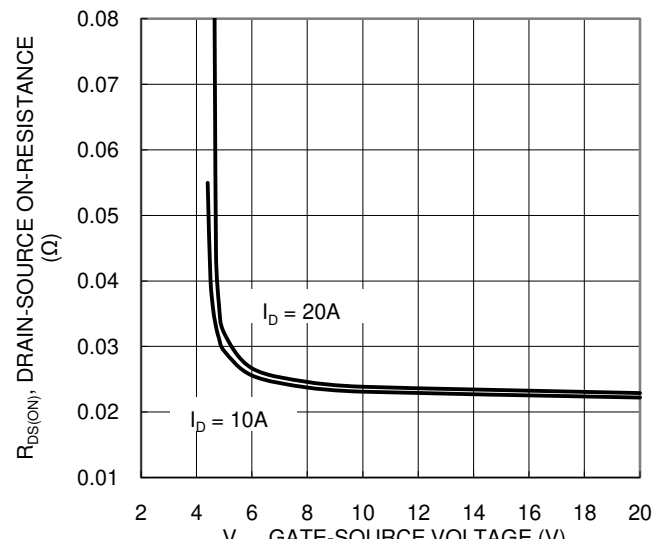


Figure 4. Typical Transfer Characteristic

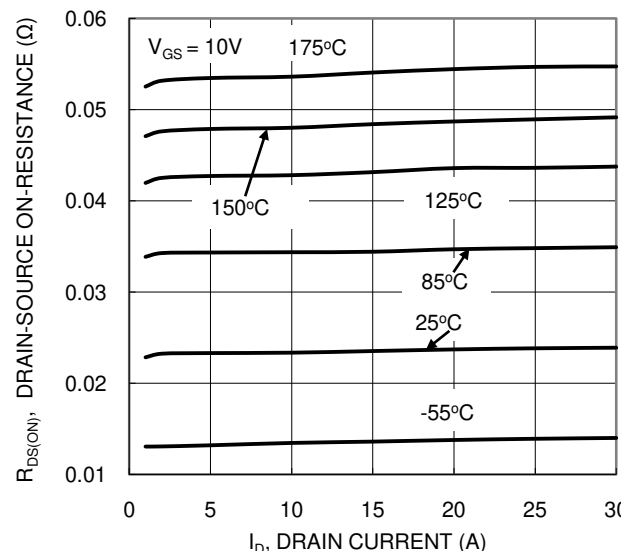


Figure 5. Typical On-Resistance vs Drain Current and Temperature

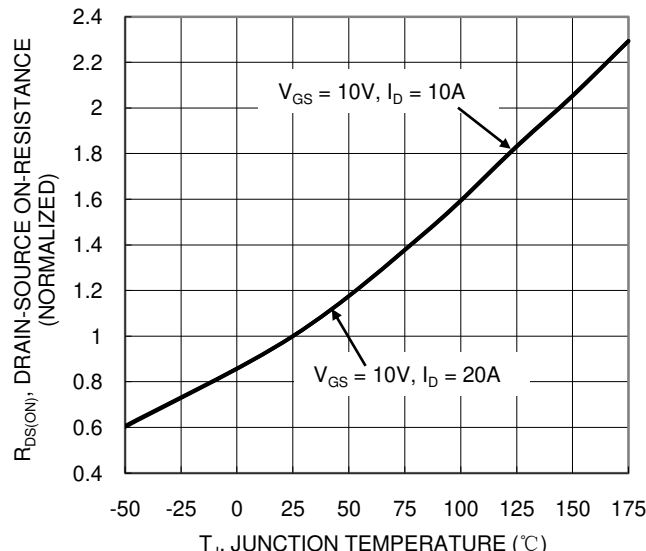


Figure 6. On-Resistance Variation with Temperature

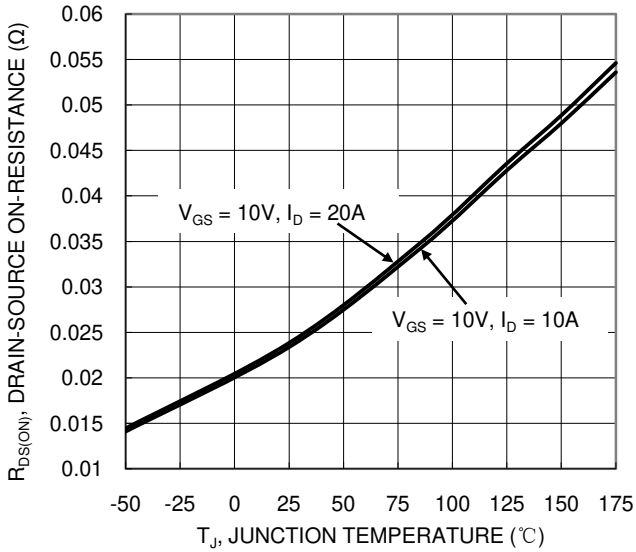


Figure 7. On-Resistance Variation with Temperature

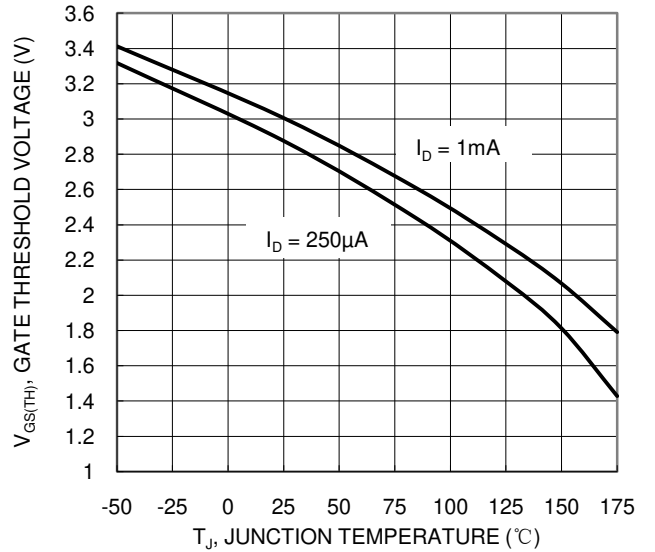


Figure 8. Gate Threshold Variation vs Junction Temperature

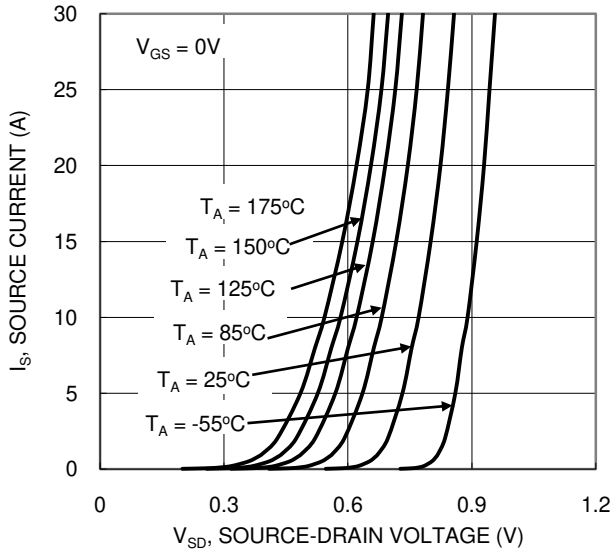


Figure 9. Diode Forward Voltage vs. Current

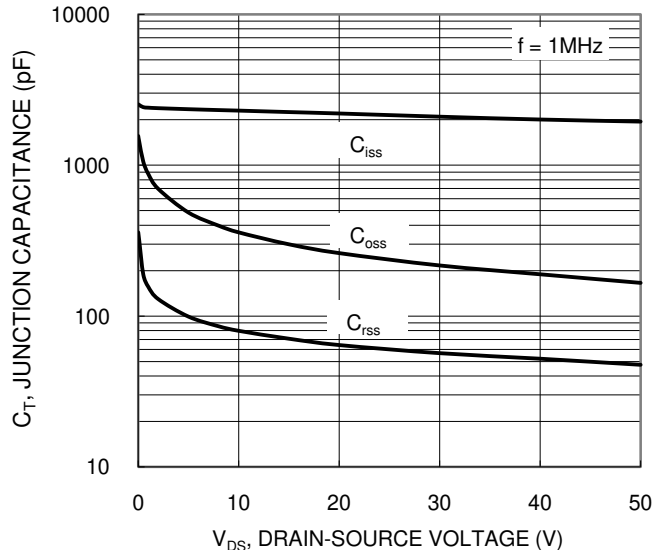


Figure 10. Typical Junction Capacitance

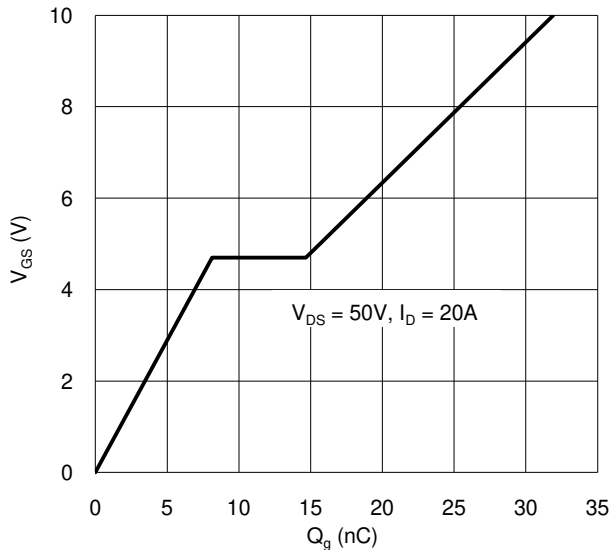


Figure 11. Gate Charge

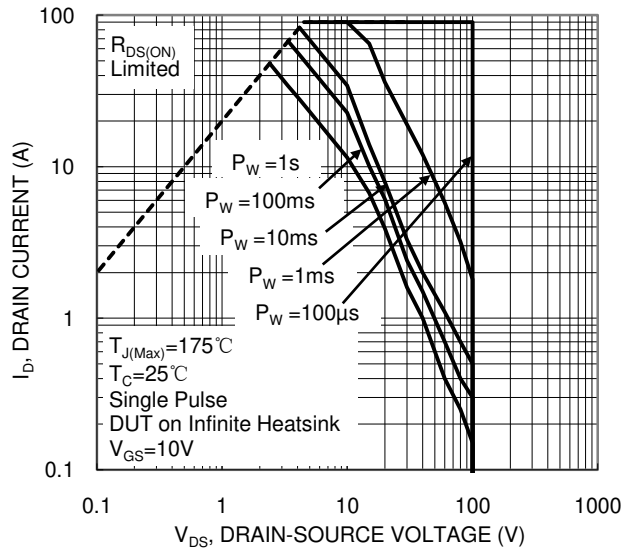
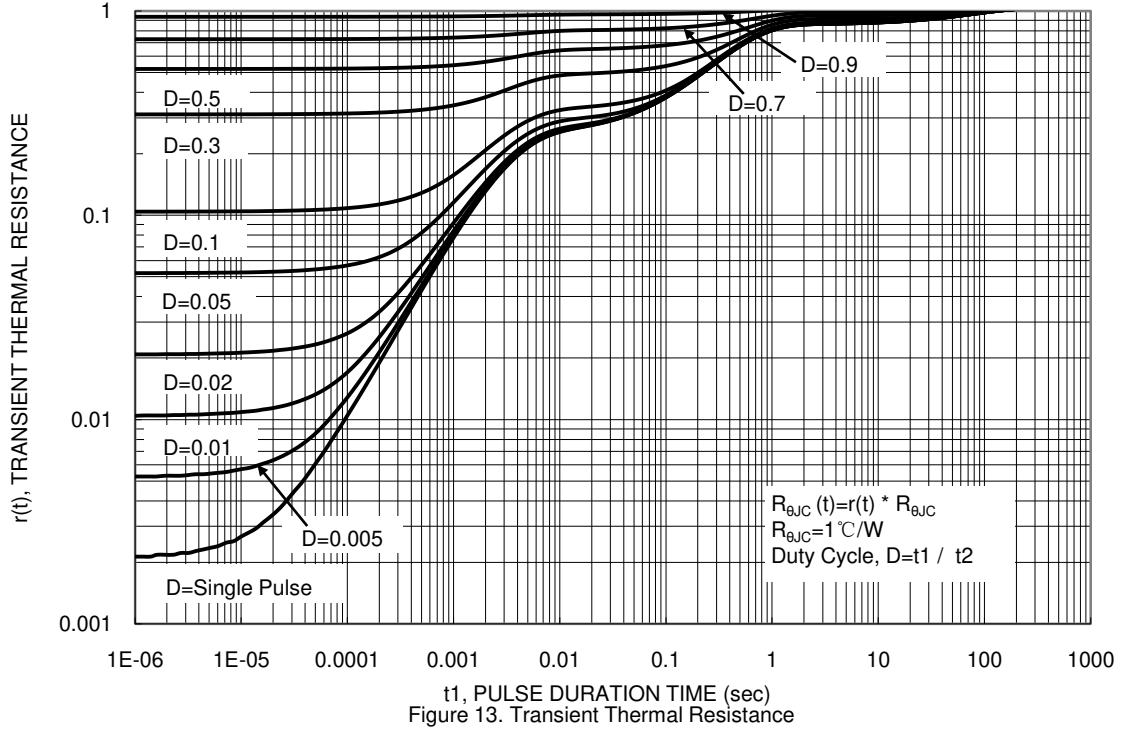


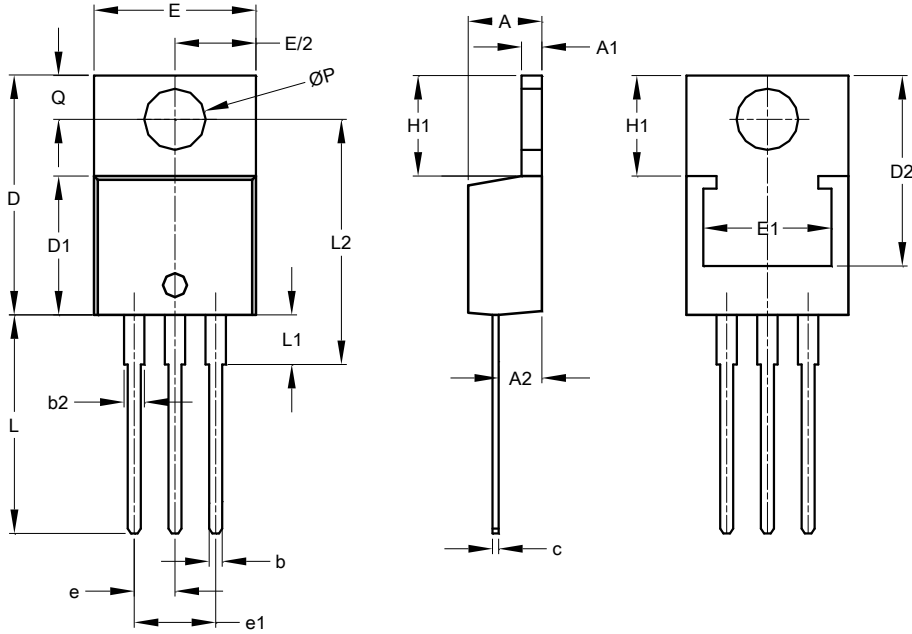
Figure 12. SOA, Safe Operation Area



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**TO220AB**



TO220AB			
Dim	Min	Max	Typ
A	3.56	4.82	-
A1	0.51	1.39	-
A2	2.04	2.92	-
b	0.39	1.01	0.81
b2	1.15	1.77	1.24
c	0.356	0.61	-
D	14.22	16.51	-
D1	8.39	9.01	-
D2	11.45	12.87	-
e	-	-	2.54
e1	-	-	5.08
E	9.66	10.66	-
E1	6.86	8.89	-
H1	5.85	6.85	-
L	12.70	14.73	-
L1	-	6.35	-
L2	15.80	16.20	16.00
P	3.54	4.08	-
Q	2.54	3.42	-
<b>All Dimensions in mm</b>			

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